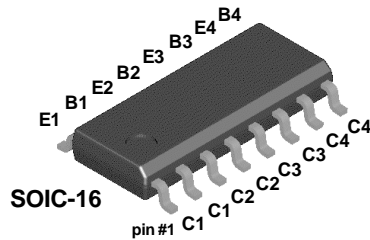


MMPQ2907



PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MMPQ2907	
P _D	Total Device Dissipation Derate above 25°C	1,000	mW
		8.0	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	125	°C/W
			°C/W
		240	°C/W

* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

** Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP General Purpose Amplifier

(continued)

MMMPQ2907

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ }\mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ }\mu\text{A}, I_C = 0$	5.0		V
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 30 \text{ V}$		50	nA
I_{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V}$		50	nA

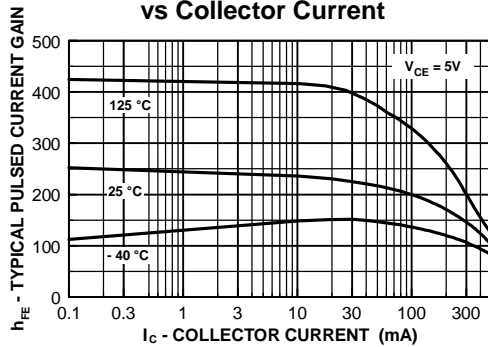
ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}^*$ $I_C = 300 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}^*$	75 100 30 50	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		0.4 1.6	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^*$ $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		1.3 2.6	V V

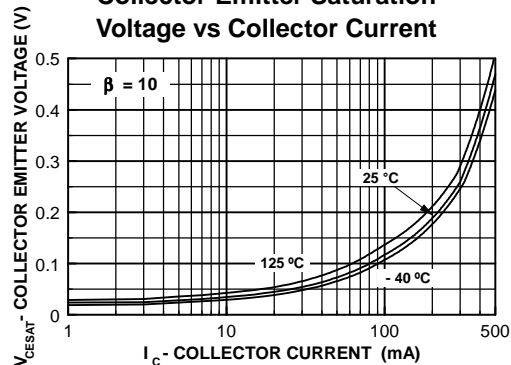
*Pulse Test: Pulse Width $\leq 300 \text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

Typical Pulsed Current Gain vs Collector Current



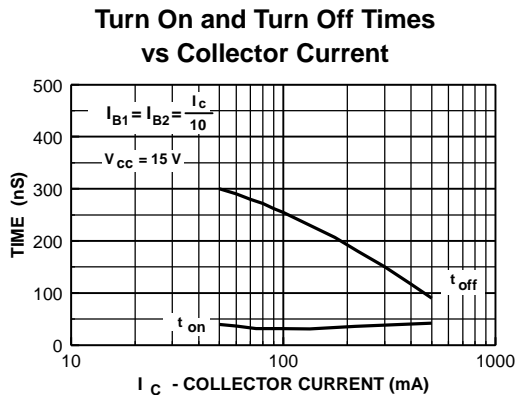
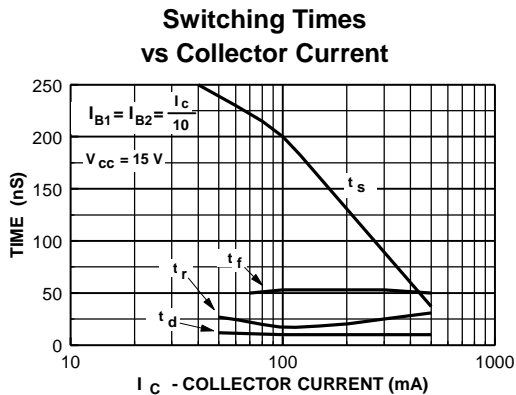
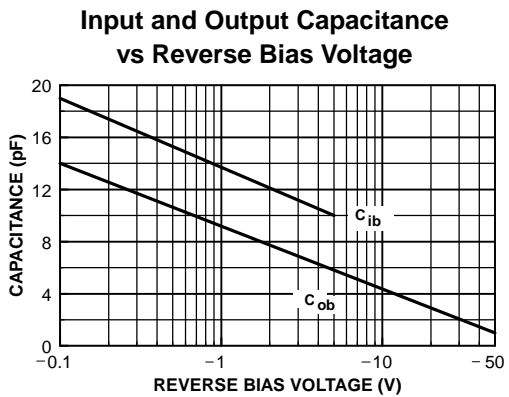
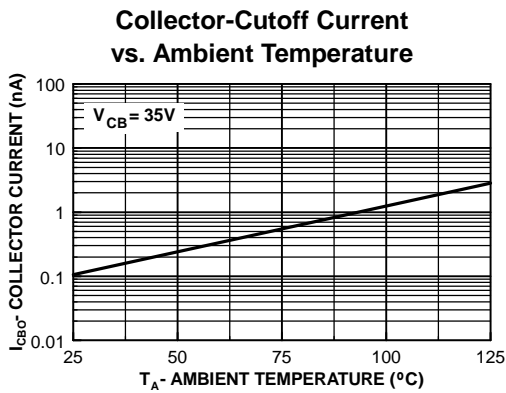
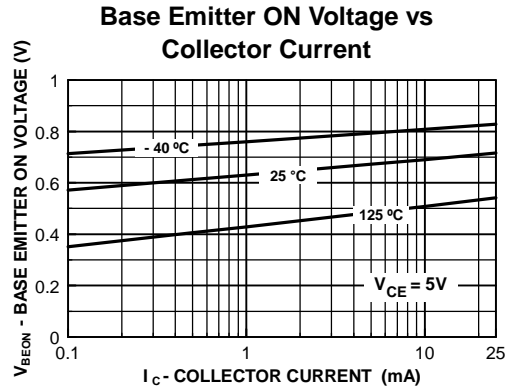
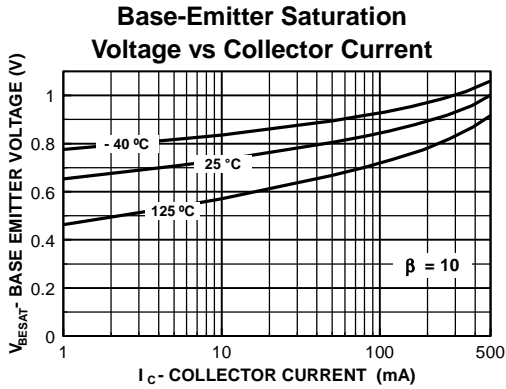
Collector-Emitter Saturation Voltage vs Collector Current



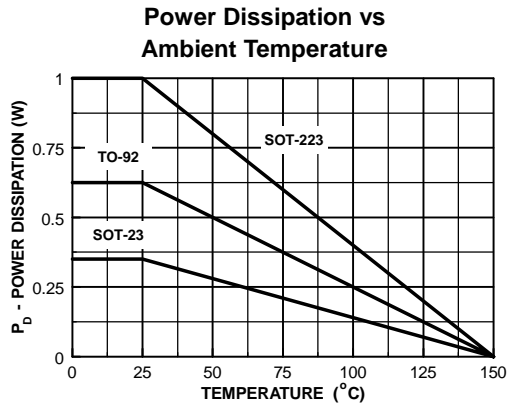
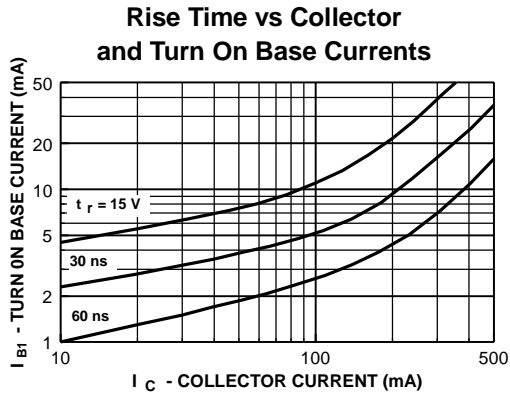
Spice Model

PNP (Is=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 Ise=54.81f Ikf=1.079 Xtb=1.5 Br=3.563 Nc=2 Isc=0 Ikr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cje=19.82p Mje=.3357 Vje=.75 Tr=111.3n Tf=603.7p Itf=.65 Vtf=5 Xtf=1.7 Rb=10)

Typical Characteristics (continued)



Typical Characteristics (continued)



Test Circuits

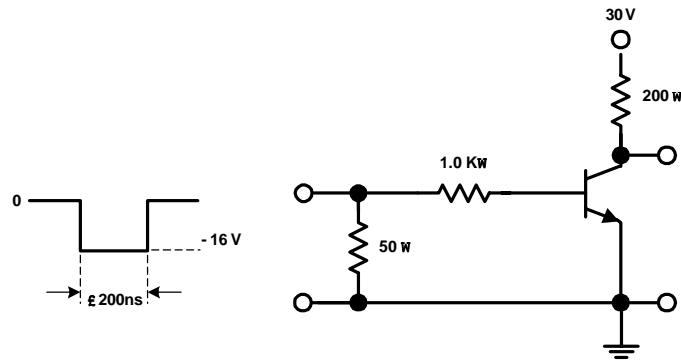


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

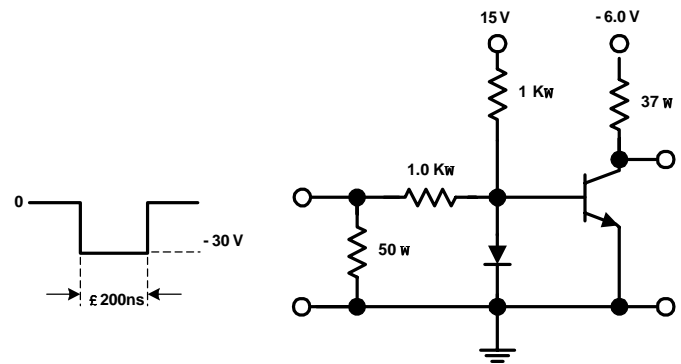


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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DenseTrench TM	HiSeC TM	QS TM	TinyLogic TM
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EcoSPARK TM	LittleFET TM	Quiet Series TM	UltraFET [®]
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